

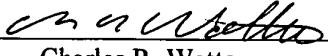
REMARKS

The above claim amendments are presented in order to remove multiple claim dependencies, so as to reduce the required filing fee.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attachment page is captioned "**Version with markings to show changes made.**"

Respectfully submitted,

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CLAIMS

1. (Delete)
2. (Delete)
- 5 3. (Amended) A method for growing a single crystal comprising arranging a blade member or a baffle member in a raw material melt in a crucible and growing a single crystal by rotating the crucible without rotating the blade member or the baffle member when growing the single crystal by bringing
10 a seed crystal into contact with the raw material melt which is heated and melted within a crucible, wherein the crystal is grown by slowly cooling the raw material melt with which the seed crystal makes contact below liquid level to precipitate a single crystal on the surface of the seed crystal.
- 15 4. (Amended) A method according to claim 3, wherein the seed crystal is also rotated while rotating the crucible.
5. (Amended) A method according to claim ~~3 or 4~~, wherein a single crystal of an oxide is grown.
6. A method according to claim 5, wherein the single
20 crystal of an oxide is a single crystal of a borate type oxide.
7. A method according to claim 6, wherein the borate type oxide is $\text{CsLiB}_5\text{O}_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $\text{CsLiB}_5\text{O}_{10}$ with at least one type among other alkali metal elements and alkali
25 earth metal elements.
8. A method according to claim 7, wherein the oxide is an oxide doped with at least one of Al and Ga elements.

9. A method according to claim 6, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_3$ ($0 < x < 1$) and the crystal is grown by a pulling method.

10. A method according to claim 5, wherein the single crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

11. (Delete)

12. (Delete)

10 13. (Amended) A growing apparatus for growing a single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, comprising a blade member or a baffle member arranged in the raw material melt in the crucible, a rotating material for
15 rotating the crucible and a cooling mechanism for slowly cooling the raw material melt, with which the seed crystal makes contact, below liquid level.

14. (Amended) A growing apparatus according to claim 13 comprising a mechanism for rotating the seed crystal.

20 15. (Amended) An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in claims 13 or 14.

16. A growing apparatus according to claim 15 being used for growing a single crystal of a borate type oxide.

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